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# MEMORY ARRAY WITH TWO-TERMINAL CROSSPOINTS USING SILICON-RICH INSULATOR

## CROSS-REFERENCE TO RELATED APPLICATION

This application is related to co-pending and commonly assigned U.S. application serial number 10/867307, filed June 14, 2004, the entire disclosure of which is incorporated herein by reference.

### TECHNICAL FIELD

This invention relates generally to arrays of memory devices and methods for their fabrication.

## 20 BACKGROUND

Markets for computers, video games, televisions, portable telephones, PDAs and other electrical devices are requiring increasingly larger amounts of memory to store images, photographs, videos, movies, music, and other storage-intensive data. At the same time, as computer and other electrical equipment prices continue to drop, the manufacturers of storage devices, such as memory devices and hard drives, need to lower the cost of their components. Thus, in addition to the need to increase the storage density of their devices,